



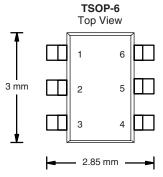
P-Channel 2.5-V (G-S) MOSFET

| PRODUCT SUMMARY | | | | |
|---------------------|--|--------------------|--|--|
| V _{DS} (V) | $R_{DS(on)}\left(\Omega\right)$ | I _D (A) | | |
| - 20 | $0.090 \text{ at V}_{GS} = -4.5 \text{ V}$ | - 2.9 | | |
| | 0.130 at V _{GS} = - 2.5 V | - 2.45 | | |

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC

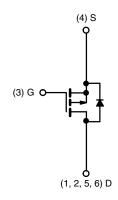




Ordering Information: Si3441BDV-T1-E3 (Lead (Pb)-free)

Si3441BDV-T1-GE3 (Lead (Pb)-free and Halogen-free)

Marking Code: B1xxx



P-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS | Γ _A = 25 °C, unles | ss otherwise n | oted | | |
|---|-------------------------------|-----------------------------------|--------------|--------------|------|
| Parameter | | Symbol | 5 s | Steady State | Unit |
| Drain-Source Voltage | | V _{DS} | - 20 | | V |
| Gate-Source Voltage | | V _{GS} | ± 8 | | |
| Outlines Paris Outline 17 450 00\d | T _A = 25 °C | - I _D | - 2.9 | - 2.45 | ^ |
| Continuous Drain Current (T _J = 150 °C) ^a | T _A = 70 °C | | - 2.35 | -1.95 | |
| Pulsed Drain Current | | I _{DM} | - 16 | | Α |
| Continuous Source Current (Diode Conduction) ^a | | I _S | - 1.0 - 0.72 | | |
| M · | T _A = 25 °C | - P _D | 1.25 | 0.86 | W |
| Maximum Power Dissipation ^a | T _A = 70 °C | | 0.8 | 0.55 | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | - 55 to 150 | | °C |

| THERMAL RESISTANCE RATINGS | | | | | |
|--|--------------|---------------------|---------|---------|------|
| Parameter | | Symbol | Typical | Maximum | Unit |
| Marrian una lumation ta Analaianta | t ≤ 5 s | - R _{thJA} | 80 | 100 | °C/W |
| Maximum Junction-to-Ambient ^a | Steady State | | 120 | 145 | |
| Maximum Junction-to-Foot (Drain) | Steady State | R_{thJF} | 70 | 85 | |

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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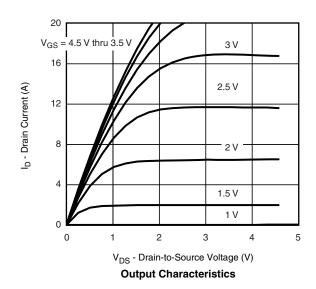
| SPECIFICATIONS T _J = 25 °C, unless otherwise noted | | | | | | | | |
|--|---------------------|---|-----------|-------|--------|------|--|--|
| Parameter | Symbol | Test Conditions | Min. Typ. | | Max. | Unit | | |
| Static | | | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = -250 \mu A$ | - 0.45 | | - 0.85 | V | | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$ | | | ± 100 | nA | | |
| Zero Gate Voltage Drain Current | | V _{DS} = - 20 V, V _{GS} = 0 V | | - 1 | | | | |
| | I _{DSS} | V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 70 °C | | | - 5 | μΑ | | |
| | I | V _{DS} = - 5 V, V _{GS} = - 4.5 V | - 10 | | | A | | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} = -5 \text{ V}, V_{GS} = -2.5 \text{ V}$ | - 4 | | | | | |
| | D | V _{GS} = - 4.5 V, I _D = - 3.3 A | | 0.070 | 0.090 | Ω | | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = - 2.5 V, I _D = - 2.9 A | | 0.098 | 0.130 | 52 | | |
| Forward Transconductance ^a | 9 _{fs} | V _{DS} = - 10 V, I _D = - 3.3 A | | 8.0 | | S | | |
| Diode Forward Voltage ^a | V_{SD} | $I_S = -1.6 \text{ A}, V_{GS} = 0 \text{ V}$ | | - 0.8 | - 1.2 | V | | |
| Dynamic ^b | | | | | | | | |
| Total Gate Charge | Qg | | | 5.2 | 8.0 | | | |
| Gate-Source Charge | Q _{gs} | $V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -3.3 \text{ A}$ | | 0.8 | | nC | | |
| Gate-Drain Charge | Q_{gd} | | | 1.5 | | 1 | | |
| Turn-On Delay Time | t _{d(on)} | | | 15 | 25 | | | |
| Rise Time | t _r | V_{DD} = - 10 V, R_L = 10 Ω | | 55 | 85 | | | |
| Turn-Off Delay Time | t _{d(off)} | $I_D \cong$ - 1.0 A, V_{GEN} = - 4.5 V, R_g = 6 Ω | | 30 | 45 | ns | | |
| Fall Time | t _f | | | 40 | 60 | | | |
| Source-Drain Reverse Recovery Time | t _{rr} | $I_F = -1.6 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$ | | 50 | 80 | | | |

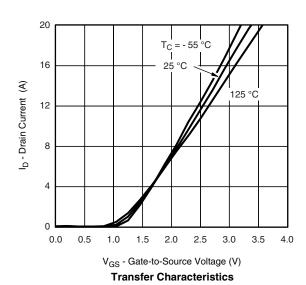
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



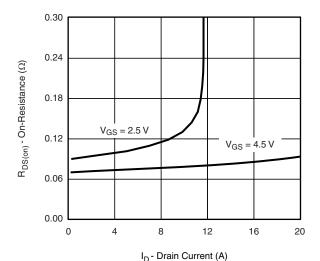




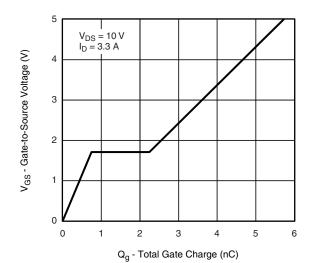




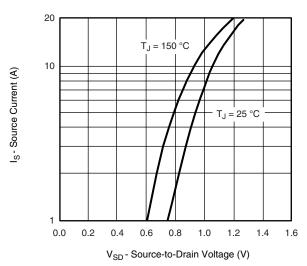
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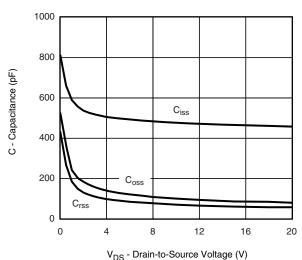
On-Resistance vs. Drain Current



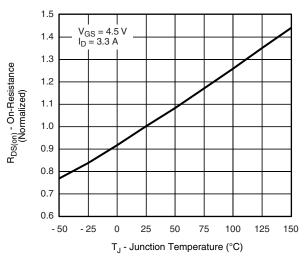
Gate Charge



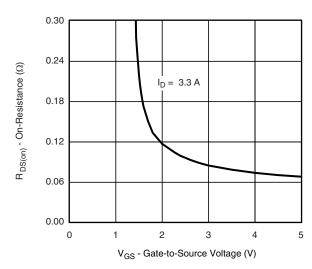
Source-Drain Diode Forward Voltage



Capacitance



On-Resistance vs. Junction Temperature

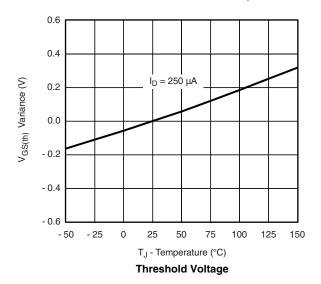


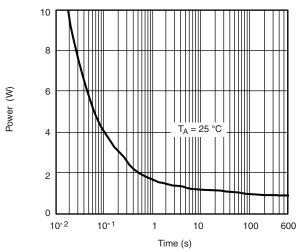
On-Resistance vs. Gate-to-Source Voltage

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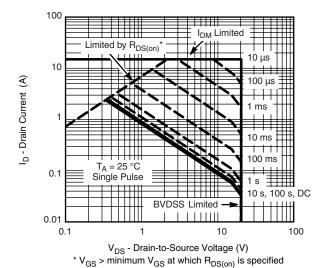
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

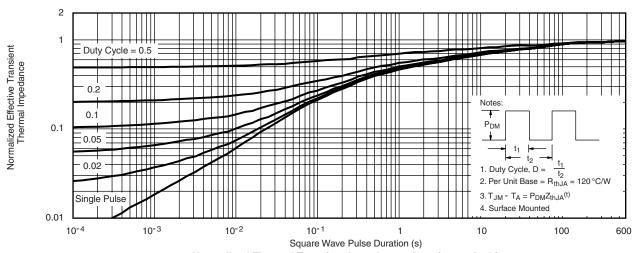




Single Pulse Power



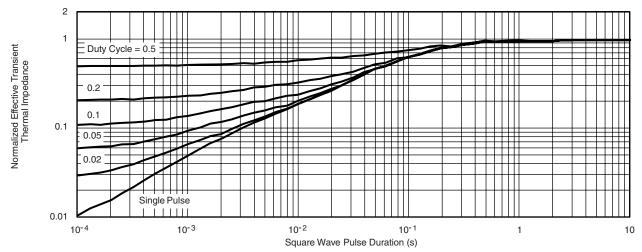
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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